

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3	((("20030231149") or ("20050092997") or ("20050095760")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 11:59
L2	363	display and laser and semiconductor adj energy adj laboratory and photograph	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:04
L3	6981	drive and zig-zag	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:01
L4	1190	3 and display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:01
L5	501	4 and channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:02
L6	188	5 and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:03
L7	139	staggered adj channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:03
L9	18	7 and semiconductor	US-PGPUB; USPAT	OR	ON	2005/05/05 12:09
L10	6057	semiconductor and ((thin adj film adj transistor) TFT) and channel\$1 and laser	US-PGPUB; USPAT	OR	ON	2005/05/05 12:11
L11	7340	((thin adj film adj transistor) TFT) and channel\$1 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:11

L12	3463	11 and display and drive	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:12
L14	2286	12 and stag\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:15
L15	2224	14 and crystal\$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:19
L16	21309	(process method) same (thin adj film adj transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:20
L17	6289	16 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:20
L18	5102	17 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:20
L19	2163	18 and "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:22
L20	1905	19 and display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:22

L22	1879	20 and crystal\$8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:25
L23	1695	22 and view	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:26
L24	159	23 and staggered	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/05 12:35
L25	1	("20040095532").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 12:36
L26	1	("20040095528").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 17:10
L27	2	((("20030231149") or ("20050092997")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 17:10
S1	5	((("20020102821") or ("20030001157") or ("6456013") or ("6194254") or ("20030067458") or ("EP1298634")). PN.	US-PGPUB; USPAT	OR	OFF	2005/05/05 11:54
S7	11	"1298634"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/21 16:00
S8	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/21 16:35
S14	5	((("6456013") or ("20030001157") or ("20020102821") or ("6194154") or ("20030067458")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/02 14:05
S17	24818	((thin adj film) TFT) and ((semiconductor adj channel\$5) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:04
S18	4238	S17 and (laser and irradiat\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:17

S20	96464	((thin adj film adj transistor\$5) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:25
S21	0	((laser adj beam\$5) and irradiat%5) same ((semiconductor adj channel\$5) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:26
S22	1795	(laser adj beam\$5) same ((semiconductor adj channel\$5) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:38
S23	532	S20 and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:28
S25	87	S23 and ("349"/\$.ccls. 257/59,72.ccls. 345/92.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:30
S26	299	((thin adj film adj transistor\$5) TFT) and (semiconductor adj channel\$5) and (semiconductor adj layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:37
S27	3123	(laser adj beam\$5) same (semiconductor adj (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 14:38
S28	14	S26 and S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 15:24
S29	1	("6495405").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/02 15:24

S30	3	("5821562" "6177301" "6211536"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/02 15:25
S31	75	(semiconductor adj channel\$5) and stripe\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:23
S39	8065	S17 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:54
S40	316	S39 and 349/42-43.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:57
S41	701	S39 and 257/59,72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:55
S42	73	S39 and 345/92.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:56
S43	608	S41 not S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:56
S44	693	S41 not S42	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:56
S45	1035	S39 and (349/42-43.ccls. 257/59,72. ccls. 345/92)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:06

S46	719	S45 not S40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 16:57
S47	77804	((thin adj film) TFT) and ((channel channels) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:05
S48	35292	((thin adj film) TFT) same ((channel channels) (semiconductor adj layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 17:20
S49	9617	S48 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/02 17:06
S50	1420	S49 and (349/42-43.ccls. 257/59,72.ccls. 345/92)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 17:25
S51	17925	((channel channels) (semiconductor adj layer)) same (stripe stripes (straight adj (line lines)) (zig-zag adj (line lines)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:16
S52	1601	S51 and ((thin adj film) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 17:24
S54	287	S52 and ("349"/\$.ccls. 257/59,72.ccls. 345/92)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 17:27
S55	2	((("5534716") or ("5808321")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/03 19:14
S56	3	((("5808321") or ("5534716") or ("6853002")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/03 19:14

S57	82770	((thin adj film) TFT) and ((channel channels) (semiconductor adj (film layer)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:17
S58	24045	S57 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:17
S59	454	S58 and 349/42-43.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:59
S60	442	S59 not S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:59
S61	136	S58 and 345/92.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 20:13
S62	135	S61 not S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 19:59
S63	1018	S58 and 257/59,72.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/03 20:13
S64	957	S63 not S54	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:51

S65	96750	((thin near film near transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:52
S66	24774	S65 and channel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:53
S67	5777	S66 and ((peripheral near circuit) (driving near circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:53
S68	5342	S67 and (crystal\$8)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 14:54
S69	881	S68 and (257/59,72,66,74.ccls.)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 16:05
S70	1	("20040218109").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 15:11
S71	5	((("20020102821") or ("20030001157") or ("6456013") or ("6194254") or ("20030067458")).PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:20
S72	19	("4466179" "4528480" "5589406" "5616506" "5712191" "5789763" "5808318" "5808595" "5824574" "5942856" "5943593" "5953597" "5981974" "6028577" "6037924" "6057183" "6096581" "6160272" "6252248").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/04 16:14
S73	0	("2003001157").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:20
S74	1	("20030001157").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:21
S75	1	("20020102821").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:21
S76	1	("6194254").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:26

S77	1945	driving adj ((thin adj film adj transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 19:27
S78	1109	S77 and channel\$1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/04 19:32
S79	1	("6303963").PN.	US-PGPUB; USPAT	OR	OFF	2005/05/04 19:32